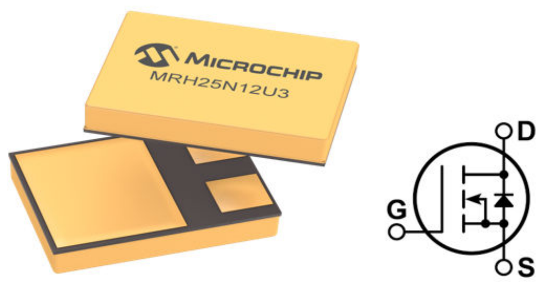
JANSR2N7593U3 M6 Technology (746)

Product Overview

Microchip's new M6 technology has been developed to provide extreme reliability and enhanced radiation hardness for hermetic Power MOSFETs targeted for space and military applications. Microchip Rad-Hard MOSFETs feature low $R_{DS(on)}$ and low total gate charge. The devices have been develeoped for Total Dose and Single-Event environments. M6 will perform in extreme-environment applications and will remain within specification in radiation evironments up to 100 krad total ionizing dose (TID).

Figure 1. MRH25N12U3/JANSR2N7593U3



U3 (SMD-0.5) Package

Features

The following are key features of the MRH25N12U3/JANSR2N7593U3 device:

- Low $R_{DS(on)}$
- Fast switching
- Single-event hardened
- Low gate charge
- Simple drive
- Ease of paralleling
- Hermetically sealed
- Surface-mount design
- Ceramic package
- ESD rating: Class 3B MIL-STD-750, TM 1020

Applications

The MRH25N12U3/JANSR2N7593U3 device is designed for the following applications:

- DC–DC converters
- Motor control
- Switch mode power supplies

1. Electrical Specifications

This section shows the electrical specifications of the MRH25N12U3/JANSR2N7593U3 device.

1.1 Absolute Maximum Ratings

The following table shows the absolute maximum ratings of the MRH25N12U3/JANSR2N7593U3 device.

Table 1-1. Absolute Maximum Ratings

Symbol	Parameter	Ratings	Unit
V_{DSS}	Drain-source voltage	250	V
I_D	Continuous drain current at T_C = 25 °C	12.4	A
	Continuous drain current at T_C = 100 °C	7.8	
I_{DM}	Pulsed drain current[1]	49.6	
V_{GS}	Gate-source voltage	±20	V
dv/dt	Peak diode recovery	5.0	V/ns
P_D	Max. power dissipation at T_C = 25 °C	75	W
	Linear derating factor	0.60	W/°C
T_J, T_{STG}	Operating junction and storage temperature range	–55 to 150	°C
T_L	Soldering temperature for 5 seconds (1.6 mm from case)	300	
W_T	Package weight	1.0	g

Note:

1. Repetitive rating: pulse width and case temperature limited by maximum junction temperature.

1.2 Electrical Performance

The following table shows the static characteristics of the MRH25N12U3/JANSR2N7593U3 device. T_A = +25 °C unless otherwise specified.

Table 1-2. Static Characteristics

Symbol	Parameter	Test Conditions		Min	Typ	Max	Unit
$V_{BR(DSS)}$	Drain-source breakdown voltage	V_{GS} = 0 V, I_D = 1.0 mA		250			V
$R_{DS(on)}$	Drain-source on resistance[1]	V_{GS} = 12 V, I_D = 7.5 A				0.210	Ω
$V_{GS(th)}$	Gate-source threshold voltage	V_{GS} =V_{DS}, I_D = 1.0 mA		2.0		4.0	V
g_{fs}	Forward transconductance	V_{DS} =15 V, I_{DS} = 7.8 A		8.8			S
I_{DSS}	Zero-gate voltage drain current	V_{DS} = 200 V V_{GS} = 0 V	T_A = 25 °C			10	μA
			T_A = 125 °C			25	

...........continued						
Symbol	**Parameter**	**Test Conditions**	**Min**	**Typ**	**Max**	**Unit**
I_{GSS}	Gate-source leakage current	V_{GS} = ±20 V			±100	nA

Note:

1. Pulse test: pulse width < 300 μs, duty cycle < 2%.

The following table shows the dynamic characteristics of the MRH25N12U3/JANSR2N7593U3 device. T_A = +25 °C unless otherwise specified.

Table 1-3. Dynamic Characteristics

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
C_{iss}	Input capacitance	V_{GS} = 0 V V_{DS} = 25 V f = 1 MHz		1980		pF
C_{rss}	Reverse transfer capacitance			6		
C_{oss}	Output capacitance			260		
Q_g	Total gate charge	V_{GS} = 12 V I_D = 12.4 A V_{DS} = 125 V		30	50	nC
Q_{gs}	Gate-source charge			11	15	
Q_{gd}	Gate-drain (”Miller”) charge			3	20	

The following table shows the switching characteristics of the MRH25N12U3/JANSR2N7593U3 device.

Table 1-4. Switching Characteristics

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
$t_{d(on)}$	Time-on delay time	V_{GS} = 12 V I_D = 12.4 A V_{DS} = 125 V $R_{G(ext)}$ = 8 Ω[1]		18		ns
t_r	Voltage rise time				30	
t_{rr}	Reverse recovery time				350	
$t_{d(off)}$	Time-off delay time				60	
t_f	Voltage fall time				30	

Note: R_G is the external gate resistance excluding internal gate driver impedance.

The following table shows the source-drain characteristics of the MRH25N12U3/JANSR2N7593U3 device. T_A = +25 °C unless otherwise specified.

Table 1-5. Source-Drain Characteristics

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
I_S	Continuous source current (body diode)	Integral reverse P-N junction diode			12.4	A
I_{SM}	Pulsed source current (body diode)[1]				49.6	
V_{SD}	Diode forward voltage[2]	I_{SD} = 12.4 A T_A = 25 °C V_{GS} = 0 V			1.2	V

...........continued						
Symbol	**Parameter**	**Test Conditions**	**Min**	**Typ**	**Max**	**Unit**
ESR	Gate equivalent source resistance	*F*=1 MHZ Level = 25 mV drain short		1.67		Ω
trr	Reverse recovery time	IF = 12.4 A di/dt ≤ 100 A/µs V_{DD} ≤ 50 V				ns

Notes:

1. Repetitive rating: pulse width and case temperature limited by maximum junction temperature.
2. Pulse test: pulse width < 300 µs, duty cycle < 2%.

The following table shows the thermal resistance of the MRH25N12U3/JANSR2N7593U3 device.

Table 1-6. Thermal Resistance

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
$R_{\Theta JC}$	Junction-to-case thermal resistance			0.56	1.67	°C/W

1.3 Typical Performance Curves

This section shows the typical performance curves of the MRH25N12U3/JANSR2N7593U3 device.

Figure 1-1. Output Characteristics

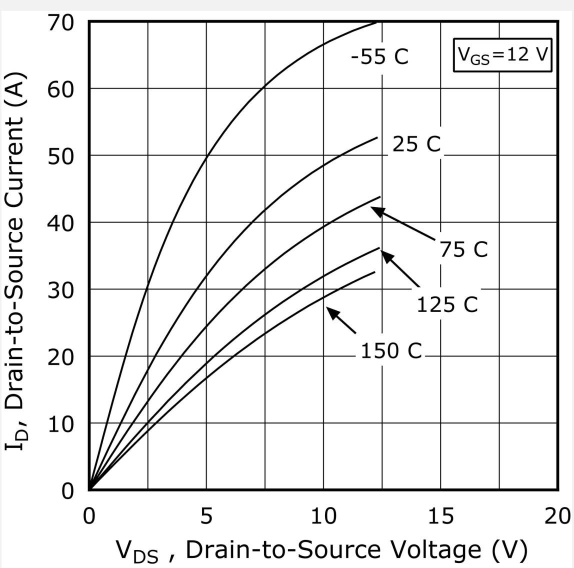


Figure 1-2. Output Characteristics at 25 °C

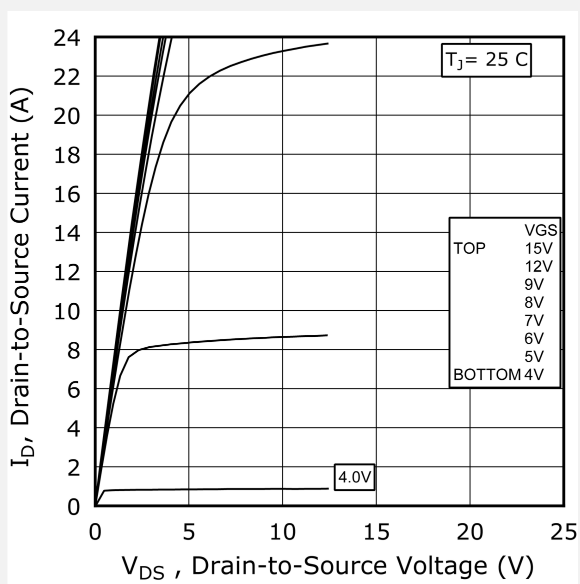


Figure 1-3. Output Characteristics at 150 °C

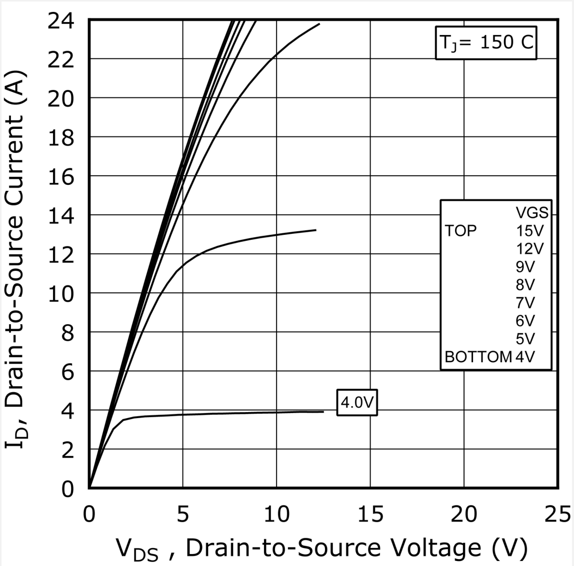


Figure 1-4. $R_{DS(on)}$ vs. Junction Temperature, 7.8 A

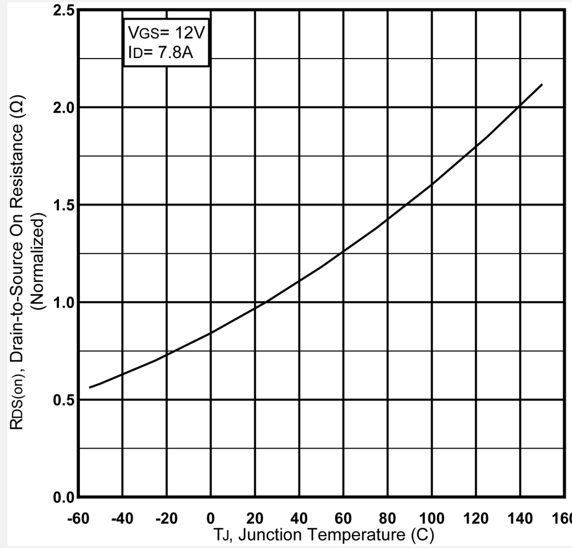


Figure 1-5. $R_{DS(on)}$ vs. Junction Temperature, 12.4 A

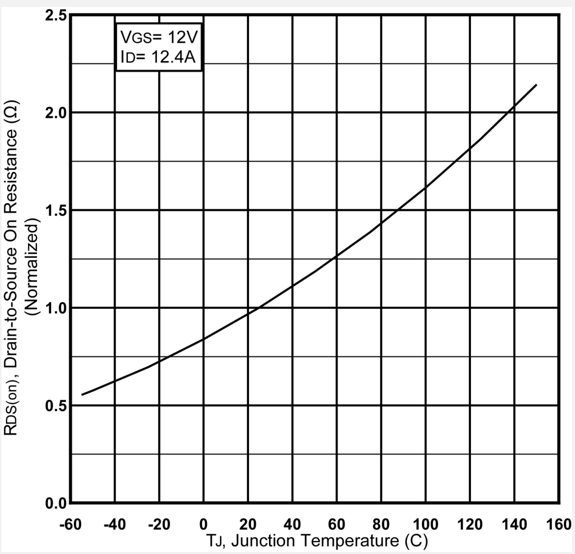


Figure 1-6. Q_G

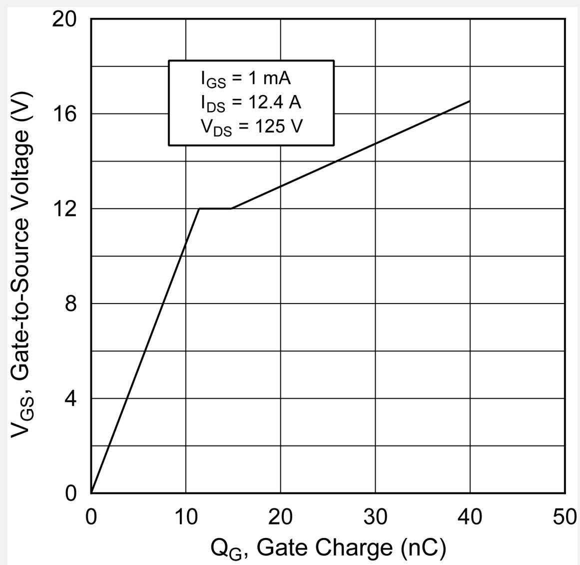


Figure 1-7. Capacitance vs. Drain-to-Source Voltage

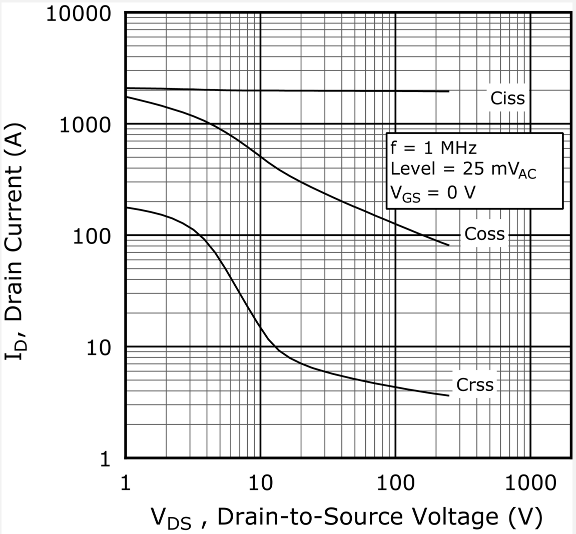


Figure 1-8. V_{GS} vs. I_D 25 °C and 150 °C

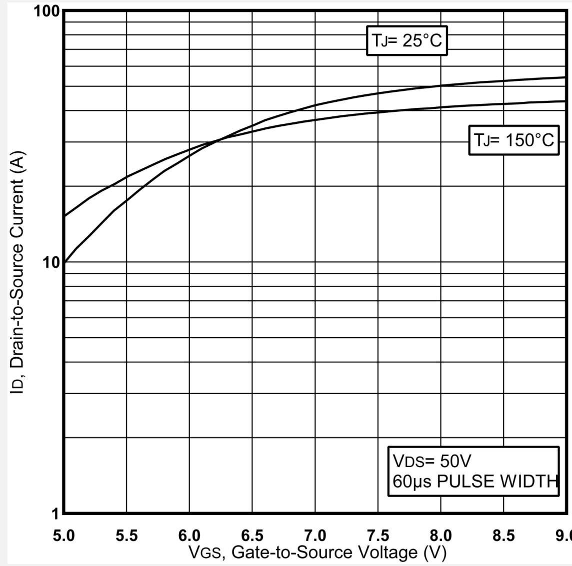


Figure 1-9. Typical Source-Drain Forward Voltage

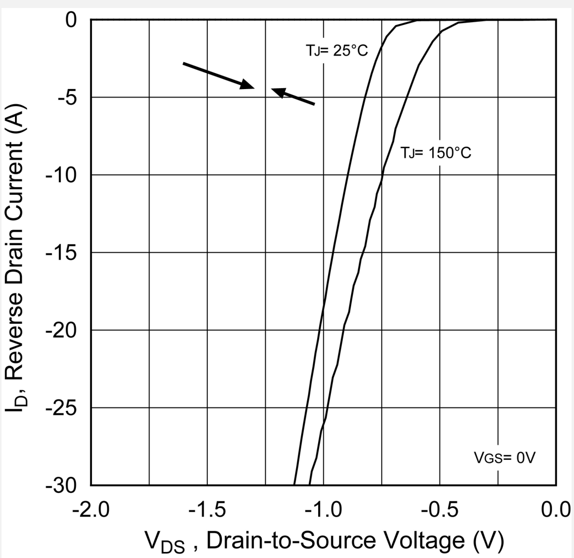


Figure 1-10. $V_{GS(th)}$ vs. Temp. Multi

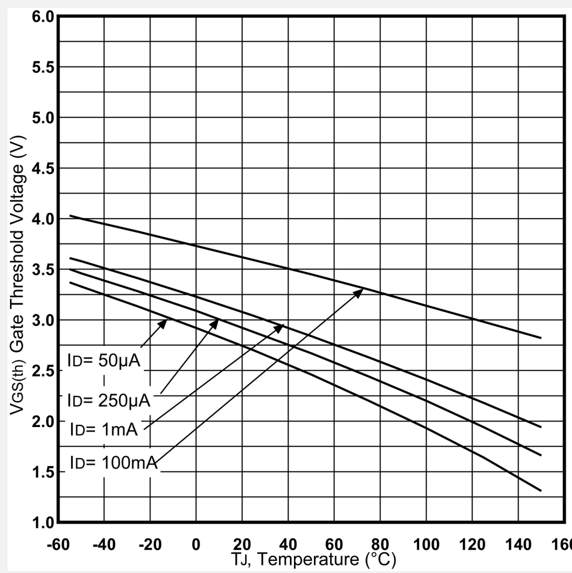


Figure 1-11. Forward Safe Operating Area

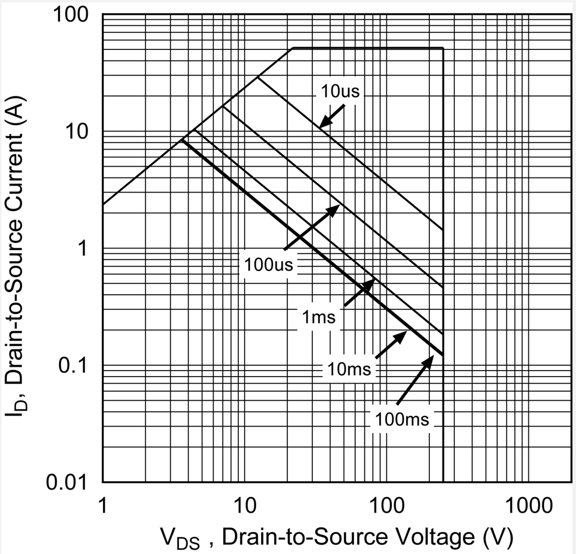


Figure 1-12. Maximum Transient Thermal Impedance

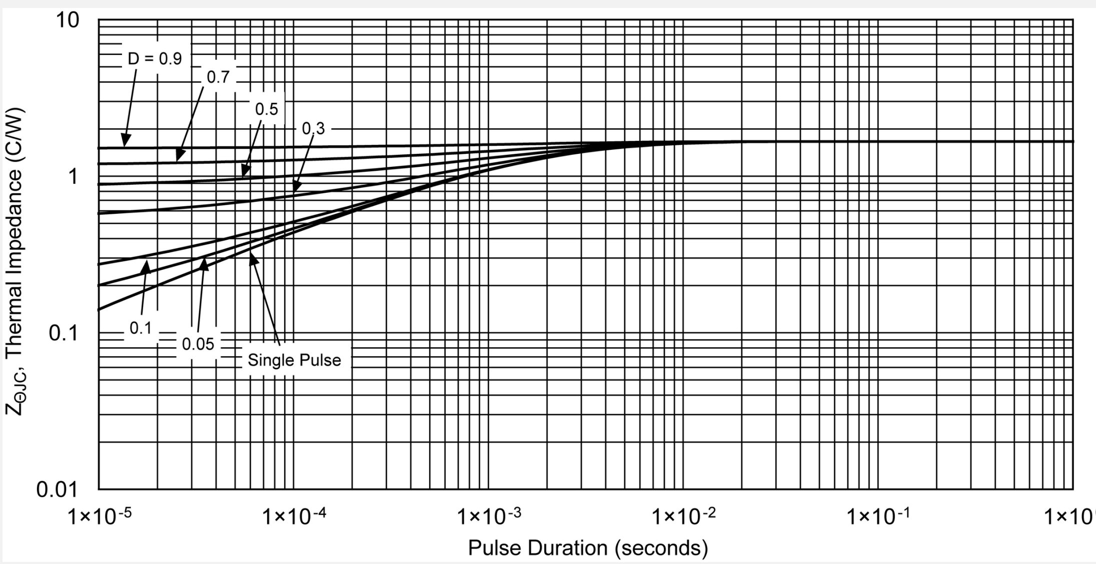


Figure 1-13. On-Resistance vs. Gate Voltage

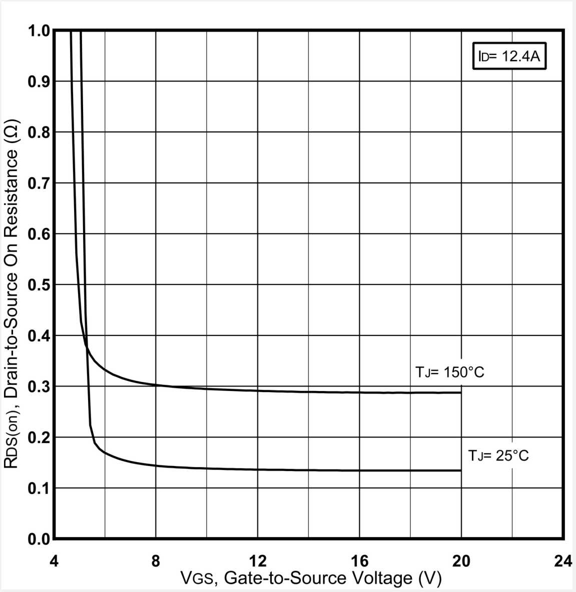


Figure 1-14. B_{Vdss} vs. Temp. I_D 1 ma

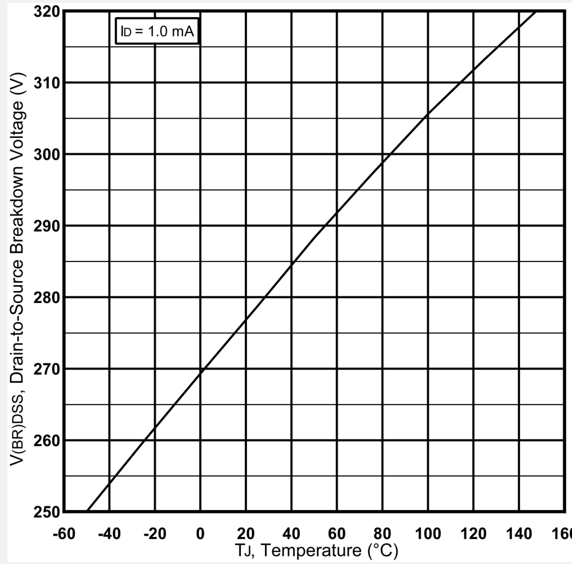


Figure 1-15. EAS vs. I_D

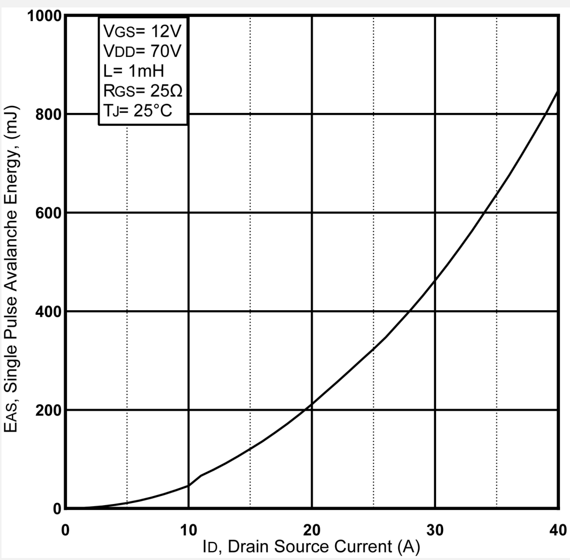


Figure 1-16. R_{DSon} vs. I_D 25 °C and 150 °C

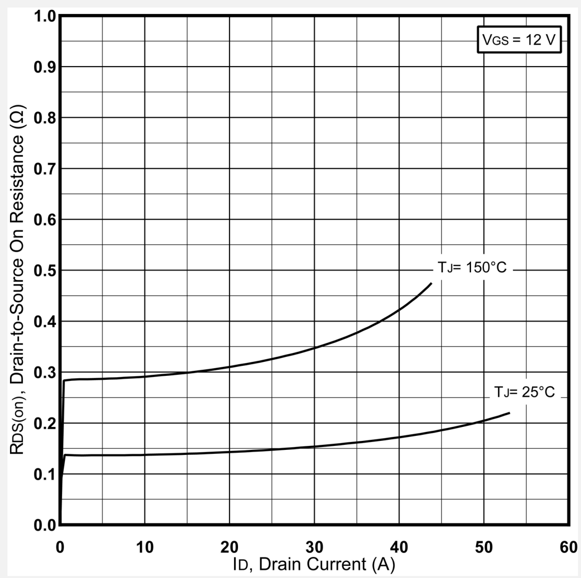
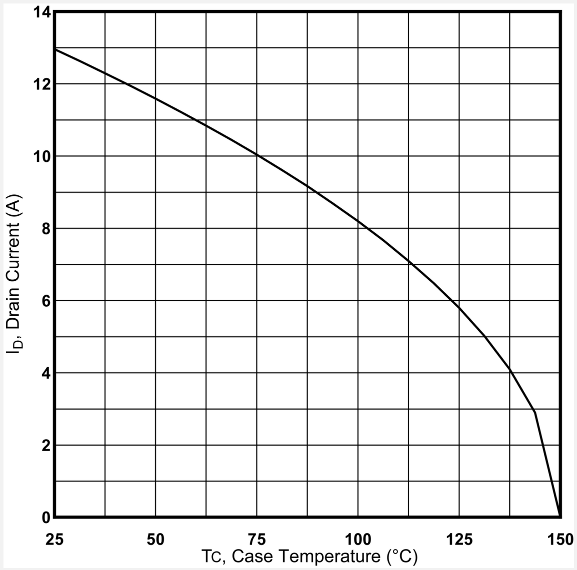


Figure 1-17. I_D vs. T_C I_D 7.8 A



2. Single-Event Effects

The Microchip MRH25N12U3/JANSR2N7593U3 device has been characterized for heavy ion responses at the Texas A&M cyclotron. Devices have been characterized up to V_{DS} = 250 V and V_{GS} = –20 V. The following single-event effects (SEE) safe-operating area profile has been established using the ions, linear energy transfer (LET), range, and total energy conditions shown.

Table 2-1. Safe-Operating Area Profile

Parameter	Description	Environment		V_{DS} (V)				
Ion species	Typical LET (MeV/(mg/cm^2))	Typ Energy (MeV)	Typ Range (µm)	V_{GS} = 0 V	V_{GS} = 5 V	V_{GS} = 10 V	V_{GS} = 15 V	V_{GS} = 20 V
Ag	44.9 (44 ±5%)	1267 (1350 ±5%)	111.2 (125 ±5%)	250	250	250	250	40
Xe	63 (61 ±5%)	1007 (825 ±5%)	74.3 (66 ±5%)	250	250	250	50	
Au	90 (90 ±5%)	1489 (1489 ±5%)	83.2 (80 ±5%)	250	250			

The following figure shows the safe-operating area of the MRH25N12U3/JANSR2N7593U3 device.

Figure 2-1. SEE Safe-Operating Area

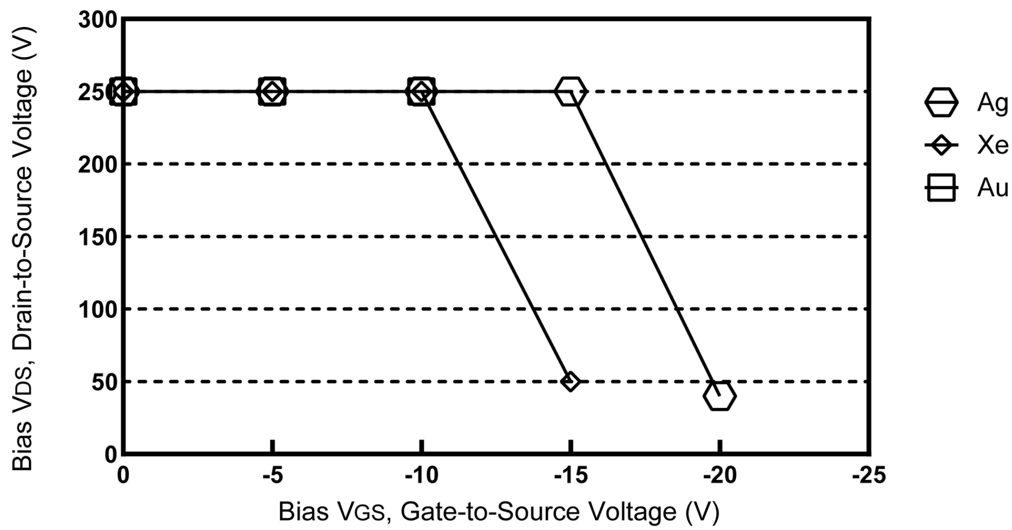
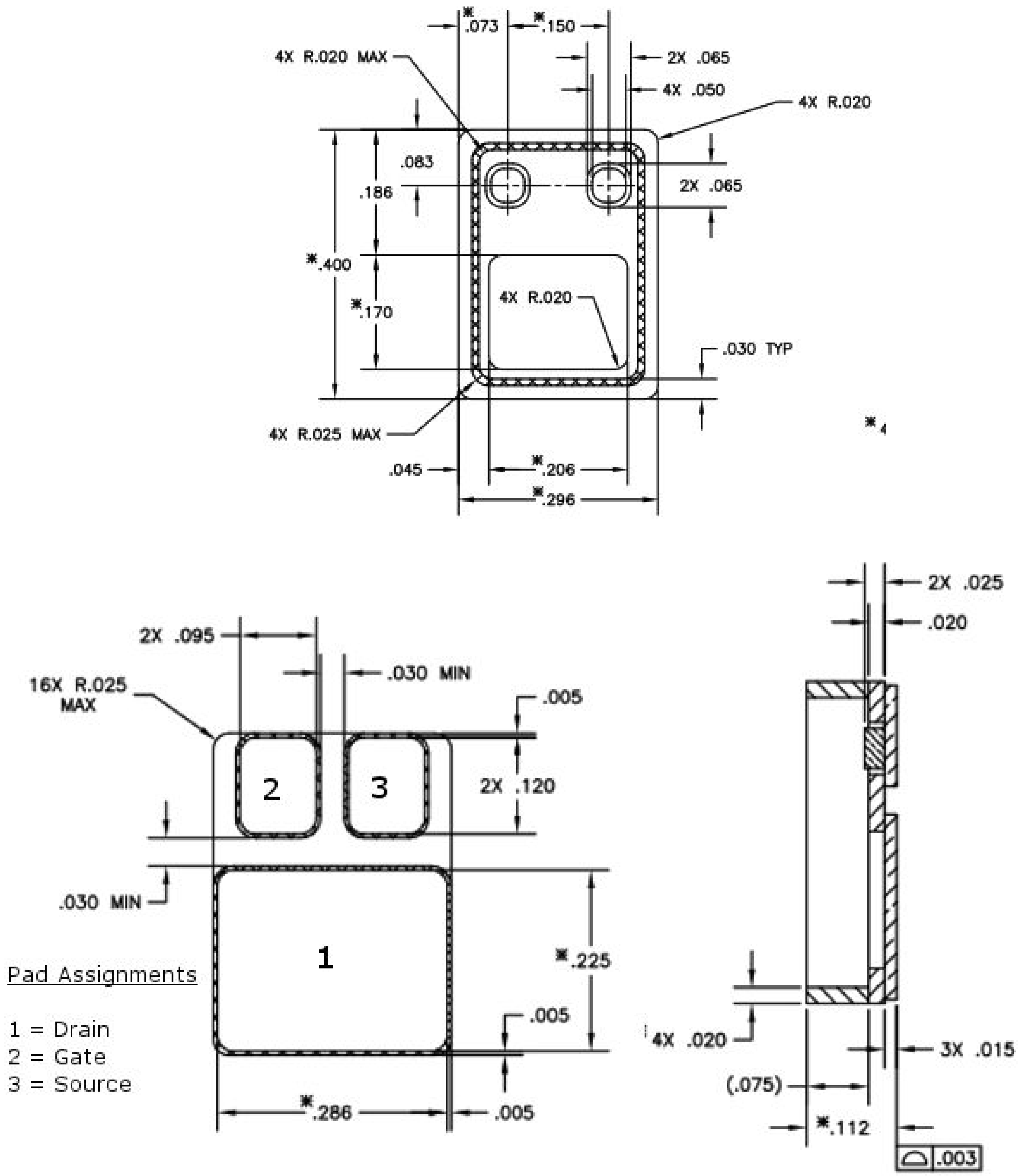


Figure 2-2. SMD.0 Case Outline and Dimensions



Microchip radiation-hardened MOSFETs are tested in a manner to provide maximum observability during heavy ion exposure. The filtering circuits of MIL-STD-750F Method 1080 are not used.

A V_{GS}/V_{DS} point is accepted on the prior plot if all of the following conditions are met:

1. A fluence of 3x105 ±20% ions/cm^2 is delivered to each sample.
2. No single-event burnout is detected via continuous monitoring of the drain current.
3. No single-event gate rupture is detected via continuous monitoring of the gate current.
4. Post-exposure IDSS tests continue to pass specification.

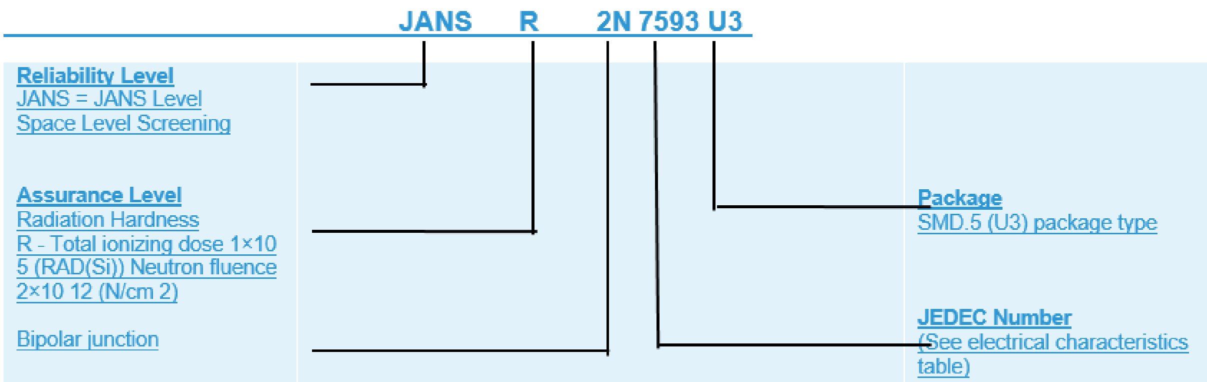
5. Post-exposure IGSS tests continue to pass specification.
6. Three randomly selected samples from different production lots are used for observation.

It should be noted that total energy levels are considered to be a factor in SEE characterization. Comparisons to other datasets should not be based on LET alone.

3. Part Nomenclature

The following image shows the part nomenclature for the JANSR2N7593U3 device. MRH25N12U3 is the internal part number.

Figure 3-1. Part Nomenclature



4. Revision History

Table 4-1. Revision History

Revision	Date	Description
A	06/2021	Document created.

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